

WHAT IS CLAIMED IS:

1. A semiconductor device comprising:
a semiconductive substrate;
a dielectric layer positioned on the semiconductive substrate; and
an interconnecting layer positioned on the dielectric layer wherein the interconnecting layer comprises a metal silicide wherein the metal is matched with the silicide so that the metal is inhibited from reacting with the dielectric layer and also wherein the metal is selected such that selective nitrification of the metal silicide lowers the work function of the metal silicide.
2. The semiconductor device of Claim 1, wherein the metal is further selected such that the metal silicide and nitrided metal silicide exhibit improved adhesion to the adjacent layers.
3. The semiconductor device of Claim 1, further comprising a conductive layer positioned on the interconnecting layer such that the dielectric layer, the interconnecting layer, and the conductive layer together define a gate stack.
4. The semiconductor device of Claim 1, wherein the metal comprises tantalum.
5. The semiconductor device of Claim 1, wherein the semiconductive substrate comprises silicon and the dielectric layer comprises silicon dioxide.
6. The semiconductor device of Claim 3, wherein the conductive layer comprises tungsten.
7. The semiconductor device of Claim 3, wherein the conductive layer comprises cobalt silicide.
8. The semiconductor device of Claim 3, wherein the conductive layer comprises nickel silicide.